L Number	Hits	Search Text	DB	Time stamp
1	73	"6140226"	USPAT;	2004/06/16 17:58
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		H.C1.4000.CH	IBM_TDB	0004/06/16 17 50
2	0	"6140226" and "Sioc-h"	USPAT;	2004/06/16 17:58
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
3	ا ما	257/758 and "SiOC-H"	USPĀT;	2004/06/16 18:01
Ĭ	Ĭ	2077 700 and 5100 ii	US-PGPUB;	2001, 00, 10 10:01
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
4	2	257/\$.ccls. and "SiOC-H"	USPĀT;	2004/06/16 18:01
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_		120/4	IBM_TDB	0004/06/16 17 50
5	3	438/\$.ccls. and "SiOC-H"	USPAT;	2004/06/16 17:59
			US-PGPUB; EPO; JPO;	
			DERWENT;	1
			IBM TDB	
6	0	361/\$.ccls. and "SiOC-H"	USPAT;	2004/06/16 17:59
~		001, 7.0010. and 0100 n	US-PGPUB;	=====================================
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
7	0	29/\$.ccls. and "SiOC-H"	USPĀT;	2004/06/16 17:59
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0004/05/15 10 00
8	0	174/\$.ccls. and "SiOC-H"	USPAT;	2004/06/16 18:00
]			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
9	3	(semiconductor or die or chip or IC) and	USPAT;	2004/06/16 18:00
-		"SiOC-H"	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
10	69	(semiconductor or die or chip or IC) and	USPĀT;	2004/06/16 18:00
		"SiOCH"	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
11		257/759 and "eiocu"	IBM_TDB USPAT;	2004/06/16 18:01
11	6	257/758 and "SiOCH"	USPAT; US-PGPUB;	2004/00/10 18:01
			EPO; JPO;	
			DERWENT;	
		·	IBM TDB	
12	43	257/\$.ccls. and "SiOCH"	USPAT;	2004/06/16 18:04
	1		US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
13	48	438/\$.ccls. and "SiOCH"	USPAT;	2004/06/16 18:04
	1		US-PGPUB;	
	1		EPO; JPO;	
	1		DERWENT;	
	077	for and 257/40	IBM_TDB	2004/06/14 01:20
-	877 1554	wafer and 257/48 257/48	USPAT USPAT	2004/06/14 01:20 2004/06/14 00:38
-	1554	25//48 "4968931".PN.	USPAT	2004/06/14 00:38
-	1	"5504369".PN.	USPAT	2004/06/14 01:02
_	1	"5898186".PN.	USPAT	2004/06/14 01:02
_	1	"5962868".PN.	USPAT	2004/06/14 01:05
Coarch His	1 - C	/16/04 6:40:20 PM Page 1		

			<u> </u>	
_	1	"6057171".PN.	USPAT	2004/06/14 01:05
-	1	"6175125".PN.	USPAT	2004/06/14 01:05
-	1	"6218848".PN.	USPAT	2004/06/14 01:05
-	1	"6281696".PN.	USPAT	2004/06/14 01:06
-	1	"6362638".PN.	USPAT	2004/06/14 01:06
-	1	"5292343".PN.	USPAT	2004/06/14 01:08
-	1	"5389556".PN.	USPAT	2004/06/14 01:09
-	1	"5391188".PN.	USPAT	2004/06/14 01:10
-	1	"5489538".PN.	USPAT	2004/06/14 01:10
-	1	"5532174".PN.	USPAT	2004/06/14 01:10
_	1	"5600257".PN.	USPAT	2004/06/14 01:11
_	1	"5532174".PN.	USPAT	2004/06/14 01:11
_	1	"5241266".PN.	USPAT	2004/06/14 01:17
_	1	"5254942".PN.	USPAT	2004/06/14 01:17
_	1	"5329471".PN.	USPAT	2004/06/14 01:18
_	1	"5396170".PN.	USPAT	2004/06/14 01:18
_	1	"5396170".PN.	USPAT	2004/06/14 01:18
_		"5408129".PN.	USPAT	2004/06/14 01:18
1 _		"5898186".PN.	USPAT	2004/06/14 01:18
]_	1	"6233184".PN.	USPAT	2004/06/14 01:18
1_	1	"6404660".PN.	USPAT	2004/06/14 01:19
_	1	"6411116".PN.	USPAT	2004/06/14 01:19
_	1	"6504359".PN.	USPAT	2004/06/14 01:19
_	47	"5389556"	USPAT	2004/06/14 01:24
_	33	"5532174"	USPAT	2004/06/14 01:24
_	9	"5327074"	USPAT	2004/06/14 02:22
_	613440	switch	USPAT	2004/00/14 02:56
_	40223	switch\$3 near transistor	USPAT	2004/06/14 02:56
	28311	switch\$3 adj transistor	USPAT	2004/06/14 02:57
_	21862	switching adj transistor	USPAT	2004/06/14 02:37
_	25	(switching adj transistor) and 257/48	USPAT	2004/06/14 03:13
	6	switching adj transistor with pad with	USPAT	2004/06/14 02:37
		(chip or dice or die)	USFAI	2004/00/14 05:14
_	1383	(chip of dice of die) 257/734	USPAT	2004/06/14 05:20
_	591	257/620	USPAT	2004/06/14 05:20
-			USPAT;	2004/06/14 05:22
-	798	257/620	1 '	2004/06/14 05:22
			US-PGPUB; EPO; JPO;	Į.
			DERWENT;	
			IBM TDB	j
	1917	257/691	USPAT;	2004/06/14 05:24
_	1917	2377691	US-PGPUB;	2004/00/14 05.24
			EPO; JPO;	
]		DERWENT;	
	E 40	257/665	IBM_TDB USPAT;	2004/06/14 05:26
-	340	257/665		2004/00/14 03:26
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			1	
	2217	257/600	IBM_TDB USPAT;	2004/06/14 05:36
-	2317	257/698		2004/00/14 05:36
			US-PGPUB; EPO; JPO;	1
			DERWENT;	
			*	
	405	257/600	IBM_TDB	2004/06/14 05:30
-	405	257/698	US-PGPUB;	2004/06/14 05:30
[EPO; JPO;	
	1		DERWENT;	
1		257/600 ==+ 257/600	IBM_TDB	2004/06/14 05:30
-	0	257/698 not 257/698	US-PGPUB;	2004/06/14 05:30
			EPO; JPO;	
			DERWENT;	
		057.4600	IBM_TDB	0004/06/11 05 5:
-	1912	257/698 not 257/698	USPAT;	2004/06/14 05:34
			US-PGPUB;	
· .			EPO; JPO;	
			DERWENT;	
	L		IBM TDB	

-	4	5494859.pn. or 6037664.pn.	USPAT;	2004/06/14 05:35
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	3299	257/773	IBM_TDB USPAT;	2004/06/14 05:45
_	3299	231/113	US-PGPUB;	2004/06/14 05:45
			EPO; JPO;	
			DERWENT;	•
			IBM TDB	
_	2690	257/773	USPĀT	2004/06/14 05:37
_	609	257/773 not 257/773	USPAT;	2004/06/14 05:39
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	849	257/735	USPAT;	2004/06/14 05:49
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	678	257/741	USPĀT;	2004/06/14 05:51
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	
-	2	5913147.pn.	USPAT;	2004/06/14 05:50
			US-PGPUB;	
İ			EPO; JPO;	
			DERWENT;	
	07.64	400/14	IBM_TDB	0004/06/14 06 00
_	2761	438/14	USPAT;	2004/06/14 06:03
			US-PGPUB;	
			EPO; JPO; DERWENT;	[
			IBM TDB	
	396	438/14	US-PGPUB;	2004/06/14 06:01
_	396	430/14	EPO; JPO;	2004/06/14 00.01
			DERWENT;	
			IBM TDB	
_	2365	438/14 not 438/14	USPAT;	2004/06/14 06:03
	2303	130,11 1100 130,11	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	863	438/462	USPAT;	2004/06/14 06:13
			US-PGPUB;	
			EPO; JPO;	
	j		DERWENT;	
			IBM_TDB	
-	221	•	USPAT;	2004/06/14 07:28
		near "N") same (silicon near dioxide or	US-PGPUB;	
		"Si" near "O.sub.2") same ("Cu" or copper)	EPO; JPO;	
			DERWENT;	
		3	IBM_TDB	0004/06/14 07 41
_	157		USPAT;	2004/06/14 07:44
		near "N") same barrier with (silicon	US-PGPUB;	
		near dioxide or "Si" near "O.sub.2") same	EPO; JPO;	
		("Cu" or copper)	DERWENT;	
_	5610	324/765	IBM_TDB USPAT;	2004/06/14 06:31
_	3610	327/103	US-PGPUB;	2004/00/14 00.31
[EPO; JPO;	
			DERWENT;	
·			IBM TDB	
_	1805	324/765	US-PGPUB;	2004/06/14 06:14
		(32.7)	EPO; JPO;	
			DERWENT;	
			IBM TDB	
	<u> </u>	L	<u>, </u>	

-	3805	324/765 not 324/765	USPAT;	2004/06/14 06:21
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1753	324/765 not 324/765 and wafer	USPAT;	2004/06/14 06:23
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
•	1004	204/7/22	IBM_TDB	2004/06/14 06:41
-	1264	324/763	USPAT;	2004/06/14 06:41
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	1290	324/760	USPAT;	2004/06/14 06:46
	1230	324/100	US-PGPUB;	2004/00/14 00:40
			EPO; JPO;	į
			DERWENT;	
			IBM TDB	
_	2	325/201	USPAT;	2004/06/14 06:50
	-	,	US-PGPUB;	-: ::, ::, 2: 00,00
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	7	barrier near multi\$4 near (film or layer)	USPAT;	2004/06/14 07:27
		same ("Cu" or copper)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	10397	barrier near (films or layers) same ("Cu"	USPAT;	2004/06/14 07:27
		or copper)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	,
-	64	(barrier with (silicon near nitride or	USPAT;	2004/06/14 07:28
		"Si" near "N") same (silicon near dioxide	US-PGPUB;	
		or "Si" near "O.sub.2") same ("Cu" or	EPO; JPO;	
		copper)) not (barrier with (silicon near	DERWENT;	
		nitride or "Si" near "N") same barrier	IBM_TDB	
		with (silicon near dioxide or "Si" near "O.sub.2") same ("Cu" or copper))		
l _	78	barrier with (silicon near nitride or "Si"	USPAT;	2004/06/14 08:00
	, ,	near "N") near (film or layer) same	US-PGPUB;	2001,00,11.00.00
		(silicon near dioxide or "Si" near	EPO; JPO;	
		"O.sub.2") near (layer or film) and ("Cu"	DERWENT;	
		or copper)	IBM TDB	
-	1	"5162258".PN.	USPĀT	2004/06/14 07:58
-	1	"5812364".PN.	USPAT	2004/06/14 07:59
-	1	"5913126".PN.	USPAT	2004/06/14 07:59
-	1	"5918135".PN.	USPAT	2004/06/14 07:59
-	1	"5920775".PN.	USPAT	2004/06/14 07:59
-	78	barrier with (silicon near nitride or	USPAT;	2004/06/14 08:00
		"Si.sub.3" near "N.sub.4") near (film or	US-PGPUB;	
		layer) same (silicon near dioxide or	EPO; JPO;	
		"Si" near "O.sub.2") near (layer or film)	DERWENT;	
		and ("Cu" or copper)	IBM_TDB	2004/06/14 20:01
-	78	barrier with (silicon near nitride or	USPAT;	2004/06/14 08:01
1		"Si.sub.3N.sub.4") near (film or layer)	US-PGPUB;	
1		same (silicon near dioxide or "Si" near "O.sub.2") near (layer or film) and ("Cu"	EPO; JPO; DERWENT;	
		or copper)	IBM TDB	
_	113	barrier same (silicon near nitride or	USPAT;	2004/06/14 08:16
	113	"Si.sub.3" near "N.sub.4") near (film or	US-PGPUB;	5501,00,11
		layer) same (silicon near dioxide or	EPO; JPO;	
		"Si" near "O.sub.2") near (layer or film)	DERWENT;	
		and ("Cu" or copper)	IBM TDB	
-	446		USPAT;	2004/06/14 08:16
		"Si.sub.3" near "N.sub.4") near (film or	US-PGPUB;	
		layer) same (silicon near dioxide or	EPO; JPO;	
		"Si" near "O.sub.2") near (layer or film)	DERWENT;	
İ		and ("Cu" or copper)	IBM TDB	

	·			
-	59	barrier and (silicon near nitride or	USPAT;	2004/06/14 08:25
		"Si.sub.3" near "N.sub.4") near (film or	US-PGPUB;	
1		layer) same (silicon near dioxide or	EPO; JPO;	
ł		"Si" near "O.sub.2") near (layer or film)	DERWENT;	
		same (passivation or protective or cover)	IBM TDB	
1			100-100	
		near (layer or film) and ("Cu" or copper)		0004/06/16 11 17
-	93	(silicon near nitride or "Si.sub.3" near	USPAT;	2004/06/16 11:17
		"N.sub.4") near (film or layer) same	US-PGPUB;	
		(silicon near dioxide or "Si" near	EPO; JPO;	
		"O.sub.2") near (layer or film) same	DERWENT;	
		(passivation or protective or cover) near	IBM TDB	
		(layer or film) and ("Cu" or copper)	100_100	
				0004/06/14 00 40
-	34	((silicon near nitride or "Si.sub.3" near	USPAT;	2004/06/14 08:42
		"N.sub.4") near (film or layer) same	US-PGPUB;	
		(silicon near dioxide or "Si" near	EPO; JPO;	
		"O.sub.2") near (layer or film) same	DERWENT;	
i		(passivation or protective or cover) near	IBM TDB	
		(layer or film) and ("Cu" or copper)) not	15155	
		(barrier and (silicon near nitride or		
		"Si.sub.3" near "N.sub.4") near (film or		
		layer) same (silicon near dioxide or		
		"Si" near "O.sub.2") near (layer or film)		
		same (passivation or protective or cover)		
		near (layer or film) and ("Cu" or copper))		
	2000		HCDAM.	2004/06/14 09:29
_	3066		USPAT;	2004/00/14 09:29
ļ		constant	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	<u> </u>
			IBM TDB	
l _	1831	silicon near nitride with dielectric near	USPAT	2004/06/14 09:38
_	1031		001111	2001,00,11 03.00
		constant		0004/06/14 00 30
-	1	("FSO") with dielectric near constant	USPAT	2004/06/14 09:39
-	1	("FSO" or "fluonated silicon oxide") with	USPAT	2004/06/14 09:39
		dielectric near constant		
l -	1	("FSO" or fluonat\$3 near silicon near	USPAT	2004/06/14 09:45
	_	oxide) with dielectric near constant		
	1	(siliconoxynitride) with dielectric near	USPAT	2004/06/14 09:40
-	1	_	OSEAL	2004/00/14 05.40
1		constant		0004/06/14 10 07
_	183		USPAT	2004/06/14 10:07
-	1605	257/750	USPAT	2004/06/14 10:12
_	2141	257/751	USPAT	2004/06/14 10:21
_	987	257/752	USPAT	2004/06/14 10:22
l <u>-</u>	3439	257/758	USPAT	2004/06/16 11:15
_	3	257/758 and (silicon near nitride or	USPAT;	2004/06/16 11:18
	1		US-PGPUB;	2001,00,10 11.10
		"Si.sub.3" near "N.sub.4") near (film or	-	1
		layer) same (silicon near dioxide or	EPO; JPO;	
		"Si" near "O.sub.2") near (layer or film)	DERWENT;	
		same (passivation or protective or cover)	IBM_TDB	
1	1	near (layer or film) and ("Cu" or copper)		
-	41		USPAT;	2004/06/16 11:24
		"Si.sub.3" near "N.sub.4") same	US-PGPUB;	
		(silicon near dioxide or "Si" near	EPO; JPO;	
1	1		DERWENT;	
		"O.sub.2") same (passivation or protective		
	i	or cover) near (layer or film) and ("Cu"	IBM_TDB	
		or copper)		
-	358	257/758 and (silicon near nitride or	USPAT;	2004/06/16 11:24
		"Si.sub.3" near "N.sub.4") same	US-PGPUB;	
		(silicon near dioxide or "Si" near	EPO; JPO;	1
		"O.sub.2") and ("Cu" or copper)	DERWENT;	
		0.3ub.2 and (ou of copper)	IBM TDB	
		052/250 /-13/ /6./4	_	2004/06/16 15:13
-	553		USPAT;	2004/06/16 15:13
1		"Si.sub.3" near "N.sub.4") and (silicon	US-PGPUB;	
				i .
		near dioxide or "Si" near "O.sub.2") and	EPO; JPO;	
		near dioxide or "Si" near "O.sub.2") and	EPO; JPO; DERWENT;	
			DERWENT;	
		near dioxide or "Si" near "O.sub.2") and ("Cu" or copper)	DERWENT; IBM_TDB	2004/06/16 12:45
-	2	near dioxide or "Si" near "O.sub.2") and ("Cu" or copper)	DERWENT; IBM_TDB USPAT;	2004/06/16 12:45
_		near dioxide or "Si" near "O.sub.2") and ("Cu" or copper)	DERWENT; IBM_TDB USPAT; US-PGPUB;	2004/06/16 12:45
_		near dioxide or "Si" near "O.sub.2") and ("Cu" or copper)	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/06/16 12:45
-		near dioxide or "Si" near "O.sub.2") and ("Cu" or copper)	DERWENT; IBM_TDB USPAT; US-PGPUB;	2004/06/16 12:45

US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; (257/758 and ("Cu" or copper)) not (257/758 and (silicon near nitride or "Si.sub.3" near "N.sub.4") and (silicon EPO; JPO; near dioxide or "Si" near "O.sub.2") and DERWENT;	04/06/16 13:16
EPO; JPO; DERWENT; IBM_TDB (257/758 and ("Cu" or copper)) not USPAT; 200 (257/758 and (silicon near nitride or US-PGPUB; "Si.sub.3" near "N.sub.4") and (silicon PEPO; JPO; near dioxide or "Si" near "O.sub.2") and DERWENT;	04/06/16 16:16
DERWENT; IBM_TDB USPAT; (257/758 and ("Cu" or copper)) not USPAT; (257/758 and (silicon near nitride or "Si.sub.3" near "N.sub.4") and (silicon per in the complex of the complex or the complex or the complex of the c	04/06/16 16:16
- 1700 (257/758 and ("Cu" or copper)) not USPAT; 200 (257/758 and (silicon near nitride or "Si.sub.3" near "N.sub.4") and (silicon per uspective in the control of the cont	04/06/16 16:16
- 1700 (257/758 and ("Cu" or copper)) not USPAT; 200 (257/758 and (silicon near nitride or US-PGPUB; "Si.sub.3" near "N.sub.4") and (silicon per EPO; JPO; near dioxide or "Si" near "O.sub.2") and DERWENT;	04/06/16 16:16
(257/758 and (silicon near nitride or US-PGPUB; "Si.sub.3" near "N.sub.4") and (silicon EPO; JPO; near dioxide or "Si" near "O.sub.2") and DERWENT;	U4/U6/16 16:16
"Si.sub.3" near "N.sub.4") and (silicon EPO; JPO; near dioxide or "Si" near "O.sub.2") and DERWENT;	
near dioxide or "Si" near "O.sub.2") and DERWENT;	
("Cull or connex")	
("Cu" or copper)) - 382 257/751 and (silicon near nitride or USPAT; 200	04/06/16 15:56
"Si.sub.3" near "N.sub.4") and (silicon US-PGPUB;)4/00/TO TO:20
near dioxide or "Si" near "O.sub.2") and EPO; JPO;	
("Cu" or copper)	
Cd of copper) DERWENT; IBM TDB	
	04/06/16 16:07
"Si.sub.3" near "N.sub.4") and (silicon US-PGPUB;	,,, oo, io io.o/
near dioxide or "Si" near "O.sub.2") and EPO; JPO;	
("Cu" or copper) DERWENT;	
IBM TDB	
	04/06/16 16:08
"Si.sub.3" near "N.sub.4") and (silicon US-PGPUB;	
near dioxide or "Si" near "O.sub.2") EPO; JPO;	
DERWENT;	
IBM TDB	
	04/06/16 16:08
"Si.sub.3" near "N.sub.4" or "SiN") and US-PGPUB;	
(silicon near dioxide or "Si" near EPO; JPO;	
"O.sub.2") DERWENT;	
IBM_TDB	
	04/06/16 16:09
"Si.sub.3" near "N.sub.4" or "SiN") and US-PGPUB;	
(silicon near dioxide or "Si" near EPO; JPO;	
"O.sub.2" or "SiO") and ("Cu" or copper) DERWENT;	
IBM_TDB	0.1.06/1.6.16.00
	04/06/16 16:09
"Si.sub.3" near "N.sub.4" or "SiN") and US-PGPUB;	
(silicon near dioxide or "Si" near EPO; JPO;	
"O.sub.2" or "SiO") and ("Cu" or copper) DERWENT;	
) not (257/758 and (silicon near nitride IBM_TDB	
or "Si.sub.3" near "N.sub.4") and	
(silicon near dioxide or "Si" near	
"O.sub.2") and ("Cu" or copper)) - 1612 257/758 not (257/758 and ("Cu" or USPAT; 200	04/06/16 17:47
1612 257/758 NOT (257/758 and ("Cu" Of USPAT; 200 US-PGPUB;	04/00/10 1/14/
Copper() US-PGPUB; EPO; JPO;	
DERWENT;	
IBM TDB	